

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
30V	0.95mΩ @ V _{GS} = 10V	130A
	1.5mΩ @ V _{GS} = 4.5V	111A

Description and Applications

This new generation MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in notebook battery power managements and load switches.

- Body control electronics
- DC-DC converters

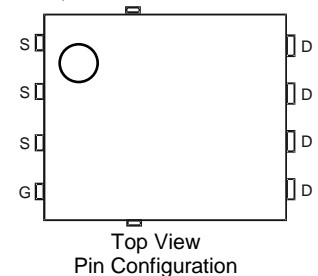
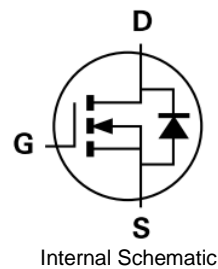
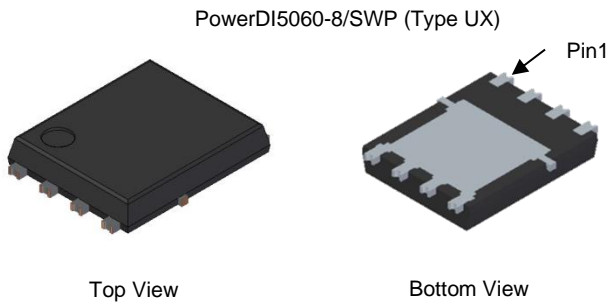
Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses < 1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMTH31M1LPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH31M1LPSWQ-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



= Manufacturer's Marking
 TH31M1LSW = Product Type Marking Code
 YYWW or YYWW = Date Code Marking
 YY or YY = Last Two Digits of Year (ex: 24 = 2024)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current, V _{GS} = 10V (Note 7)	I _D	T _C = +25°C T _C = +70°C	130 111	A
Continuous Drain Current, V _{GS} = 10V (Note 6)		T _A = +25°C T _A = +70°C	40 32	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	500	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	4.2	A	
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)	I _{SM}	500	A	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	76	A	
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	296	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	1.8	W	
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	70	°C/W
Total Power Dissipation (Note 6)		P _D	3	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	42	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	3.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{DS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	—	2.3	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.7	0.95	mΩ	V _{GS} = 10V, I _D = 30A
		—	0.9	1.5		V _{GS} = 4.5V, I _D = 30A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 30A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	5938	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	4806	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	201	—	pF	
Gate Resistance	R _g	—	0.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	86	—	nC	V _{DS} = 15V, I _D = 30A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	39	—	nC	
Gate-Source Charge	Q _{gs}	—	13	—	nC	
Gate-Drain Charge	Q _{gd}	—	7	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	12	—	ns	V _{DD} = 15V, V _{GEN} = 10V, R _{GEN} = 4.7Ω, I _D = 30A
Turn-On Rise Time	t _r	—	28	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	82	—	ns	
Turn-Off Fall Time	t _f	—	45	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

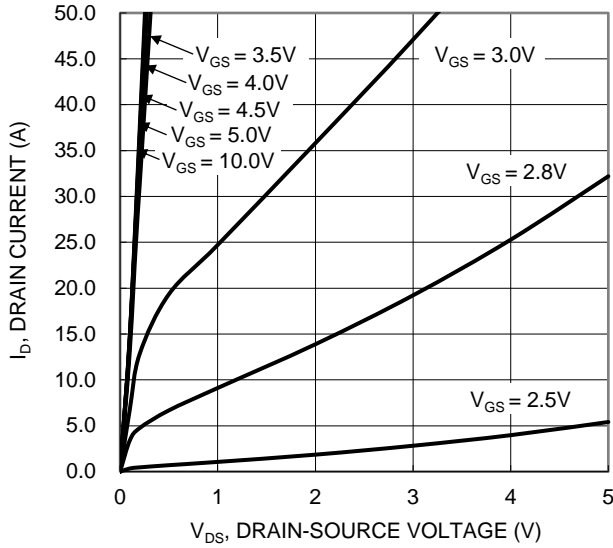


Figure 1. Typical Output Characteristic

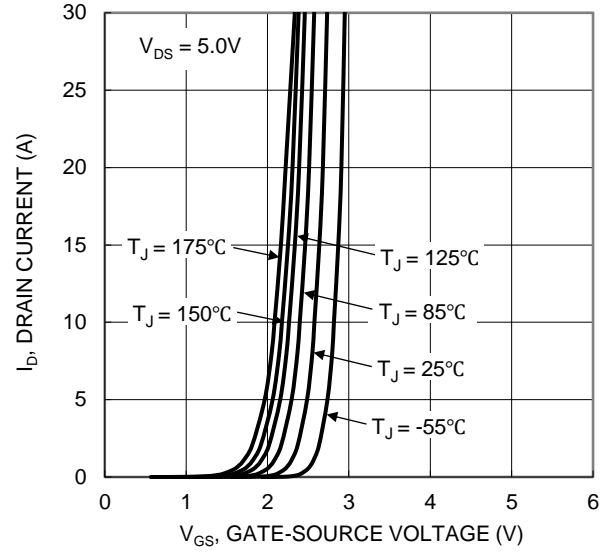


Figure 2. Typical Transfer Characteristic

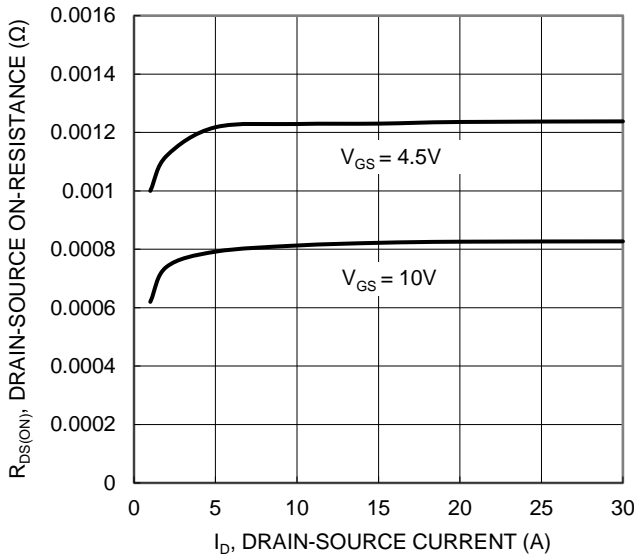


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

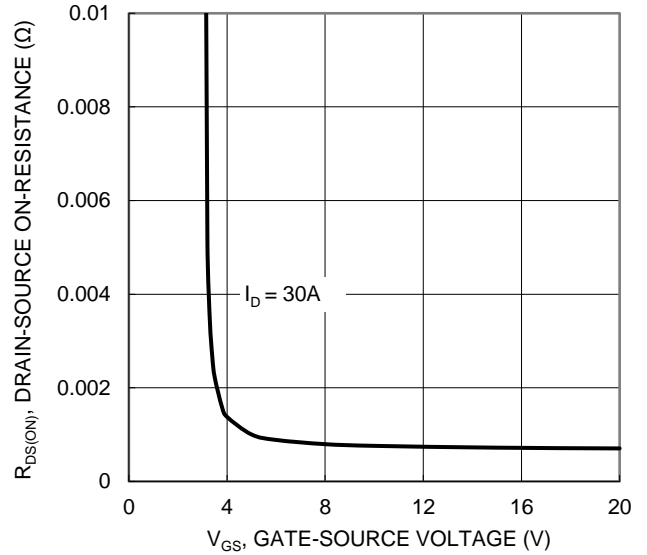


Figure 4. Typical Transfer Characteristic

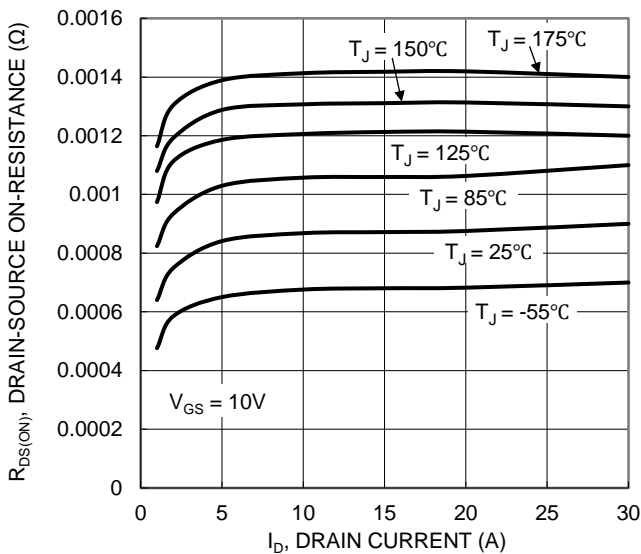


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

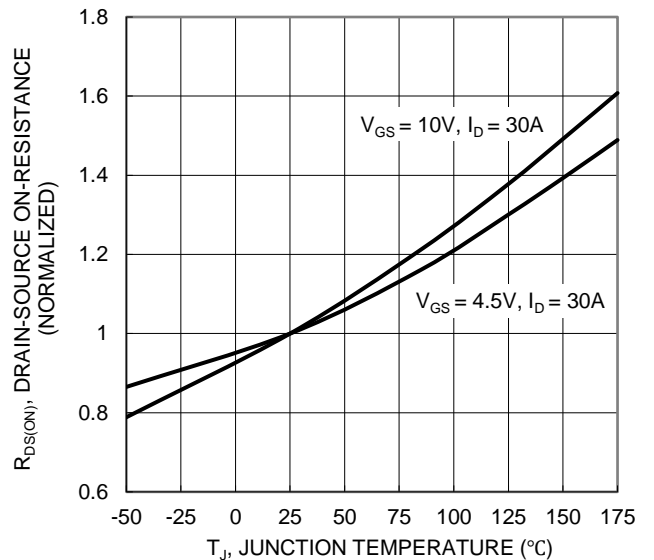


Figure 6. On-Resistance Variation with Junction Temperature

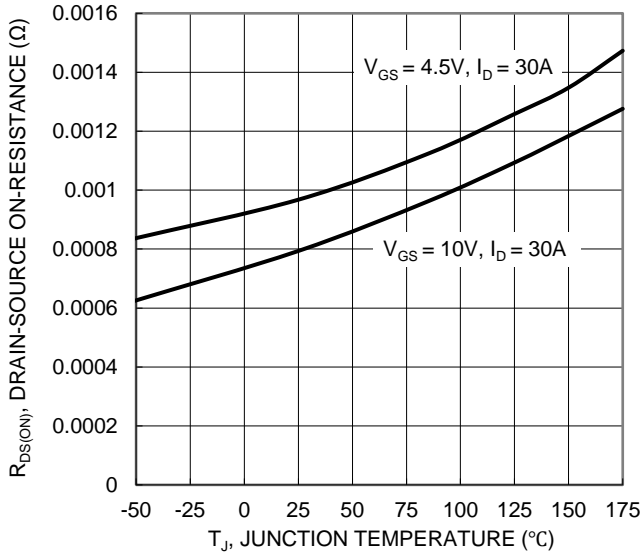


Figure 7. On-Resistance Variation with Junction Temperature

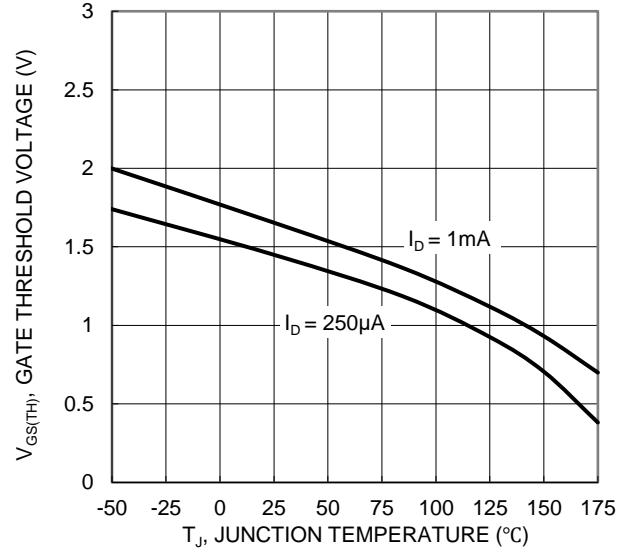


Figure 8. Gate Threshold Variation vs. Junction Temperature

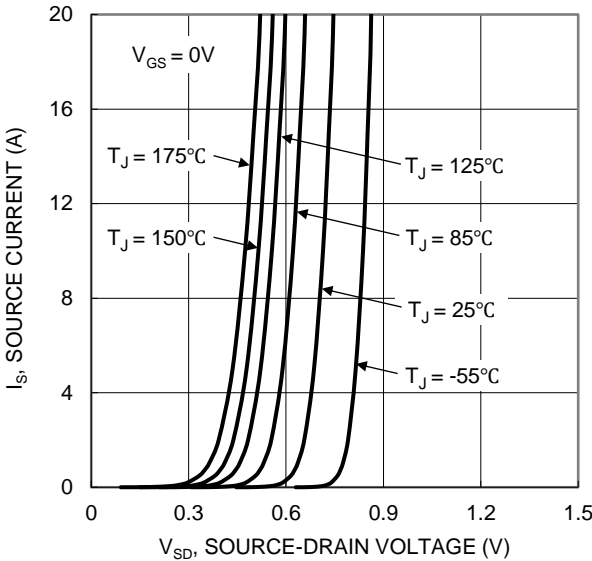


Figure 9. Diode Forward Voltage vs. Current

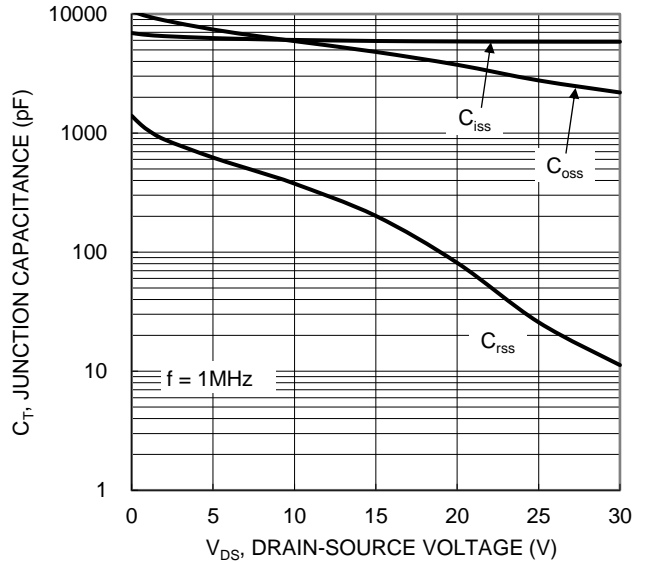


Figure 10. Typical Junction Capacitance

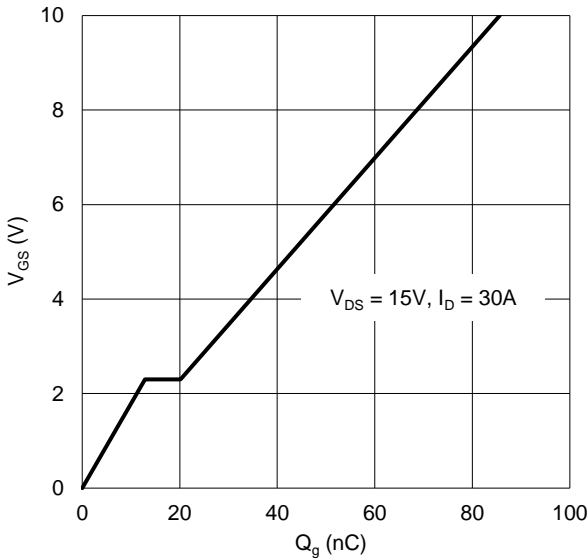


Figure 11. Gate Charge

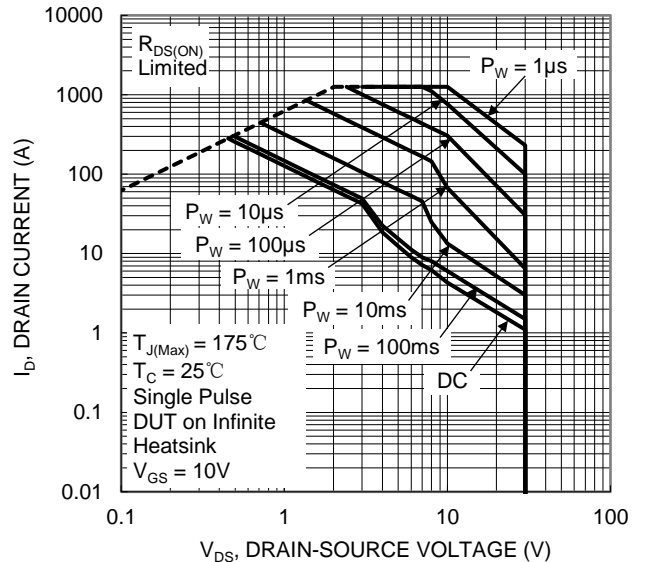


Figure 12. SOA, Safe Operation Area

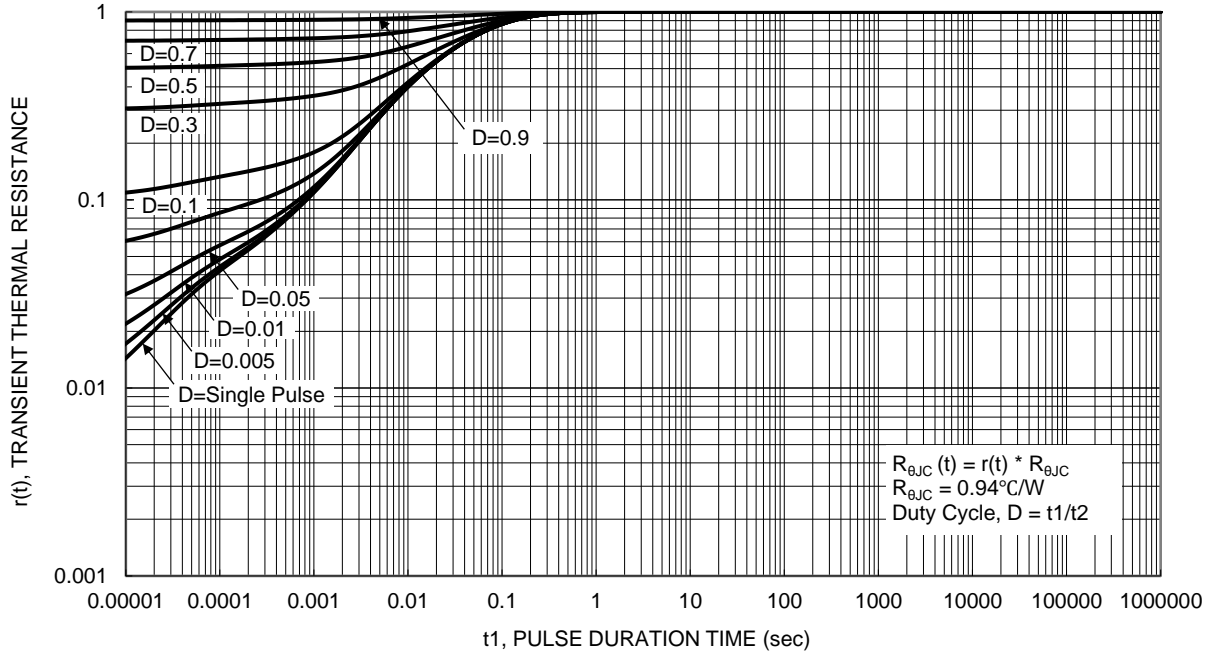


Figure 13. Transient Thermal Resistance

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